

Power Transistor 2SB1622

Absolute Maximum Ratings (Ta=25°C)

Symbol	Ratings	Unit
V _{CB0}	-200	V
V _{CE0}	-200	V
V _{EB0}	-5	V
I _C	-15	A
I _B	-1	A
P _C	85 (T _C =25°C)	W
T _J	150	°C
T _{stg}	-55 to +150	°C

Electrical Characteristics (Ta=25°C)

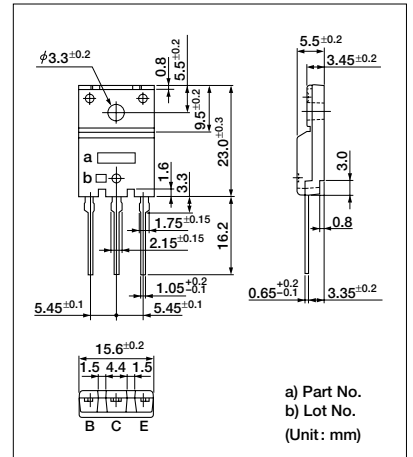
Symbol	Test Conditions	Ratings			Unit
		min	typ	max	
I _{CB0}	V _{CB} = -200V			-100	μA
I _{EB0}	V _{EB} = -5V			-100	μA
V _{CE0}	I _C = -30mA	-200			V
h _{FE} *	V _{CE} = -4V, I _C = -10A	5000		30000	
V _{CE(sat)}	I _C = -10A, I _B = -10mA			-2.5	V
V _{BE(sat)}	I _C = -10A, I _B = -10mA			-3.0	V
f _T	V _{CE} = -12V, I _E = 2A		60		MHz
C _{OB}	V _{CB} = -10V, f = 1MHz		270		pF

*Rank: O(5000 to 12000), P(6500 to 20000), Y(15000 to 30000)

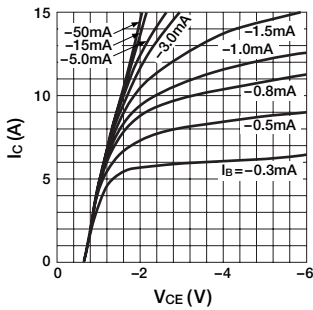
Typical Switching Characteristics

V _{CC} (V)	R _L (Ω)	I _C (A)	V _{BB1} (V)	V _{BB2} (V)	I _{B1} (mA)	I _{B2} (mA)	t _{on} (μs)	t _{stg} (μs)	t _f (μs)
-40	4	-10	-10	5	-10	10	0.4typ	3.6typ	1.0typ

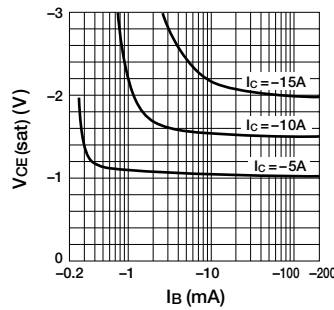
External Dimensions



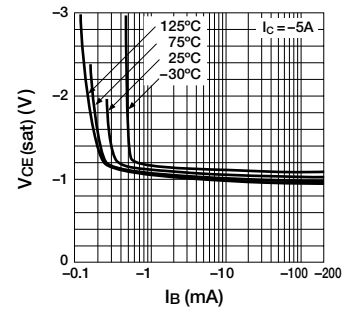
■ I_C—V_{CE} Characteristics (typ.)



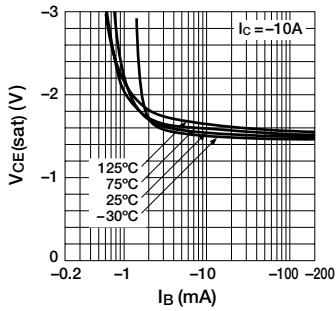
■ V_{CE(sat)}—I_B Characteristics (typ.)



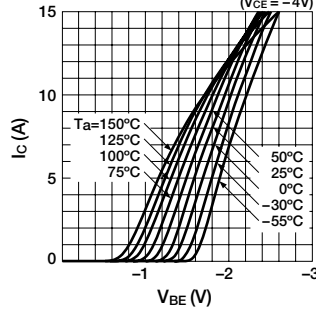
■ V_{CE(sat)}—I_B Temperature Characteristics (typ.)



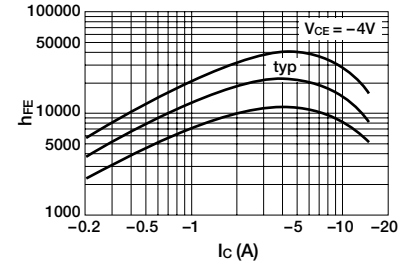
■ V_{CE(sat)}—I_B Temperature Characteristics (typ.)



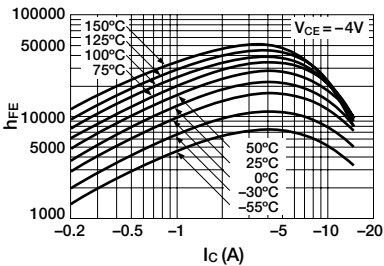
■ I_C—V_{BE} Temperature Characteristics (typ.)



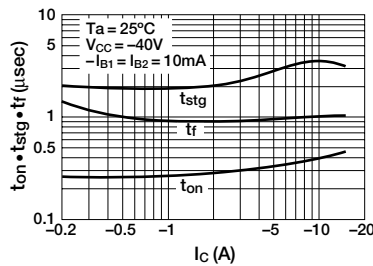
■ h_{FE}—I_C Characteristics (typ.)



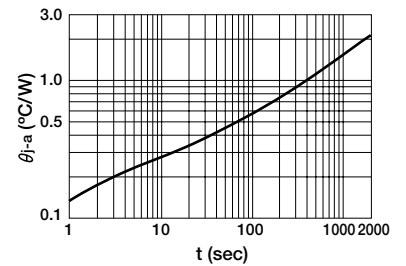
■ h_{FE}—I_C Temperature Characteristics (typ.)



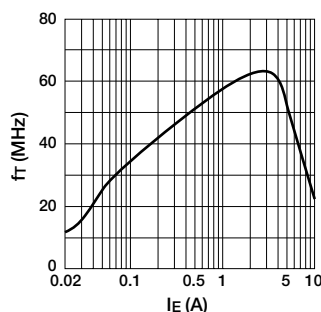
■ t_{on}•t_{stg}•t_f—I_C Characteristics (typ.)



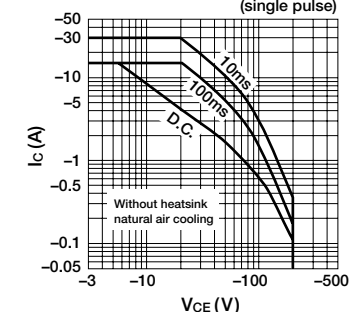
■ θ_{j-a}—t Characteristics



■ f_T—I_E Characteristics (typ.)



■ Safe Operating Area



■ P_C—T_a Derating

